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	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
APPLICATION NO.	FIEING DATE		0057-2533-2Y	3815	
09/421,217	10/20/1999	HIDEKI TAKAHASHI	0057-2555-21	3013	

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7590

09/24/2003

OBLON, SPIVAK, MCCLELLAND, MAIER & NEUSTADT, P.C.

1940 DUKE STREET ALEXANDRIA, VA 22314 EXAMINER

LOKE, STEVEN HO YIN

PAPER NUMBER ART UNIT

2811

DATE MAILED: 09/24/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

PTO-90C (Rev. 07-01)

<u>;,</u>		Application N	<u>. </u>	Applicant(s)					
Office Action Summary		09/421,217		TAKAHASHI, HIDEKI					
		Examin r		Art Unit					
		Steven Loke		2811					
	Th MAILING DATE of this communication ap	pears on the co	er sheet with the	correspondence	address				
Peri	nd for Renly								
- -	A SHORTENED STATUTORY PERIOD FOR REPLIFIE MAILING DATE OF THIS COMMUNICATION. Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. If the period for reply specified above is less than thirty (30) days, a replif NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailinearned patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, h	owever, may a reply be to minimum of thirty (30) doine SIX (6) MONTHS from the become ABANDON	timely filed ays will be considered tin m the mailing date of thi NFD (35 U.S.C. § 133).	nely. s communication.				
	1) Responsive to communication(s) filed on 21	July 2003 .							
	a)⊠ This action is FINAI 2b)□ T	his action is no	n-final.		the merits is				
	3) Since this application is in condition for allow closed in accordance with the practice unde	vance except fo er <i>Ex part</i> e Quay	r formal matters, /le, 1935 C.D. 11	, 453 O.G. 213.) the ments is				
טוS 	position of Claims 4)⊠ Claim(s) <u>40-44</u> is/are pending in the applicat	tion.							
	4a) Of the above claim(s) is/are withdr	awn from consi	deration.						
	5) Claim(s) is/are allowed.								
	6)⊠ Claim(s) <u>40-44</u> is/are rejected.								
	7) Claim(s) is/are objected to.								
	8) Claim(s) are subject to restriction and	I/or election req	uirement.						
Ap	plication Papers								
	9)☐ The specification is objected to by the Examin	ner.		·					
	10) The drawing(s) filed on is/are: a) acc	cepted or b) o	ojected to by the	xaminer See 37 CFR 1 85	i(a)				
	Applicant may not request that any objection to	the drawing(s) b	e held in abeyance	proved by the Exa	aminer.				
	Applicant may not request that any objection to	is: a)L_l app	oroved b) disap	pproved by the Ext					
If approved, corrected drawings are required in reply to this Office action.									
	12)☐ The oath or declaration is objected to by the	Examiner.							
Pr	iority under 35 U.S.C. §§ 119 and 120		05 11 5 0 8 11	19(a)-(d) or (f)					
	13) Acknowledgment is made of a claim for fore	eign prionty und	er 35 U.S.C. 9 11	19(a)-(d) 01 (1).					
	a)□ All b)□ Some * c)□ None of:		المستديد						
	1. Certified copies of the priority docume	ents have been	received in Appl	ication No					
	2. Certified copies of the priority docume	ents have been	received in Appl	coived in this Nati	onal Stage				
	Copies of the certified copies of the papplication from the International See the attached detailed Office action for a	list of the certifi	ed copies not rec	eived.					
	* See the attached detailed Office action to a set of a s								
	a) ☐ The translation of the foreign language provisional application has been received. 15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.								
A	ttachment(s)								
1 2	Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No	s) o(s)	4) Interview Sur 5) Notice of Info 6) Other:	mmary (PTO-413) Pa ormal Patent Applicati	oer No(s) on (PTO-152)				

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1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

2. Claims 40, 42 and 44 are rejected under 35 U.S.C. 102(e) as being clearly anticipated by Kinzer.

In regards to claim 40, Kinzer shows all the elements of the claimed invention in fig.

20. It is an insulated gate semiconductor device, comprises: a first semiconductor layer ([50] of fig. 19) of a first conductivity type (p) having first and second main surfaces on opposite sides thereof; a second semiconductor layer ([52] of fig. 20) of a second conductivity type (n) provided on the first main surface of the first semiconductor layer; a third semiconductor layer [180] of the second conductivity type higher in an impurity concentration (n+) and thinner than the second semiconductor layer [52], and provided on a surface of the second semiconductor layer [52]; a fourth semiconductor layer [81] of the first conductivity type provided on a surface of the third semiconductor layer [61, 62], wherein the third semiconductor layer [180] is interposed between the second semiconductor layer [52] and a bottom of the fourth semiconductor layer [81], and said third semiconductor layer [180] is in direct contact with said second semiconductor layer [52] and so that fourth semiconductor layer [81] does not contact with second semiconductor layer [52]; a fifth semiconductor layer [131] of the second conductivity

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type selectively provided in a surface of the fourth semiconductor layer [81] and opposing the third semiconductor layer [180] through the fourth semiconductor layer [81]; a first main electrode [160] disposed across and connected with surfaces of the fourth and fifth semiconductor layers [81, 131]; a second main electrode [170] provided on the second main surface of the first semiconductor layer [50]; an insulating film [111, 112] provided on portions of the fourth semiconductor layer [81] interposed between the third and fifth semiconductor layers [180, 131]; a control electrode [114, 115] facing the portions through the insulating film [111, 112] so that the portions form channel regions of the insulated gate semiconductor device, and the fourth semiconductor layer [81] is the only semiconductor layer where the channel regions are formed.

Since Kinzer discloses his device has a hexagonal cell topology (col. 9, lines 44-59), the insulating film [110, 111, 112] is a continuous insulating film and the gate electrode [113, 114, 115] is a continuous gate electrode.

In regards to claim 42, Kinzer further discloses a sixth semiconductor layer ([51] of fig. 19) of the second conductivity type higher in an impurity concentration (n+) than the second semiconductor layer [52] provided between the first and second semiconductor layers ([50, 52] of fig. 19).

In regards to claim 44, Kinzer further discloses the first main electrode [160] is not contacting any other semiconductor than the fourth and fifth semiconductor layers [81, 131].

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

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(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

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4. Claims 41 and 43 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kinzer.

In regards to claim 41, Kinzer differs from the claimed invention by not showing the second semiconductor layer extends through the first semiconductor layer and is partially exposed in the second main surface of the first semiconductor layer. It would have been obvious for the second semiconductor layer extends through the first semiconductor layer and is partially exposed in the second main surface of the first semiconductor layer because it depends to the switching speed of the device.

In regards to claim 43, Kinzer differs from the claimed invention by not showing the sixth semiconductor layer extends through the first semiconductor layer and is partially exposed in the second main surface of the first semiconductor layer. It would have been obvious for the sixth semiconductor layer extends through the first semiconductor layer and is partially exposed in the second main surface of the first semiconductor layer because it depends to the switching speed of the device.

5. Applicant's arguments filed 7/21/03 have been fully considered but they are not persuasive.

It is urged, in page 4 of the remarks, that Kinzer never discloses the fourth semiconductor layer does not contact with the second semiconductor layer. However, as shown in fig. 20 of Kinzer, the fourth semiconductor layer [81] does not contact with

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40.

the second semiconductor layer [52]. Therefore, Kinzer shows all the elements of claim

6. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven Loke whose telephone number is (703) 308-4920. The examiner can normally be reached on 7:50 am to 5:20 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (703) 308-2772. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

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September 22, 2003

Steven Loke Primary Examples Steven Sohe